



FORM PTO-1449 (Modified)	Attorney Docket No.: 108-18.1	Application No.: 10/777,560
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	Applicant: Harry S. Luan, et al.	
	Filing Date: February 11, 2004	Group:

Reference Designation	U.S. PATENT DOCUMENTS	Page 1
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Examiner Initial	Document No.	Date	Name	Class	Sub-class	Filing Date (If Appropriate)
<u>HN</u> AA	6,204,139	3/20/01	Liu et al	438	385	
<u>HN</u> AB	6,531,371	3/11/03	Hsu et al	438	385	
AC						
AD						
AE						
AF						
AG						
AH						
AI						
AJ						
AK						
AL						
AM						
AN						
AO						

FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Class	Sub-class	Translation (Yes/No)

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)
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<u>HN</u> AP	Zhuang et al., "Novell Colossal Magnetoresistive Thin Film Nonvolatile Resistance Random Access Memory (RRAM)," IEEE 2002.
<u>HN</u> AQ	Liu et al., "A New Concept for Non-Volatile Memory: The Electric Pulse Induced Resistive Change Effect in Colossal Magnetoresistive Thin Films,"
<u>HN</u> AR	Liu et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films," American Institute of Physics, 2000, pg. 2749-2751.
AS	
AT	
AU	
AV	
AW	
AX	

EXAMINER <u>[Signature]</u>	DATE CONSIDERED <u>3/26/2006</u>
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.